Listing of Claims:

1. (original) A semiconductor device comprising:

a substrate having conductive interconnections;

two or more vertically stacked chips on said substrate, each supporting chip having metal standoffs thereon to separate it from the next successive chip; and

a plurality of bond wires connecting at least one chip to said substrate.

2. (original) A semiconductor device as in claim 1, wherein said metal standoffs comprise aluminum islands.

3. (original) A semiconductor device as in claim 1, wherein the thickness of said metal standoffs is 5 to 20 kA.

4. (original) The semiconductor device of claim 1 wherein said standoffs are patterned over the chip passivation layer.

5- The semiconductor device of claim 1 wherein said metal standoffs are thermally conductive.

6. (original) The semiconductor device of claim 1 wherein said metal standoffs are positioned within the area surrounded by bond pads.

7. (original) The semiconductor device of claim 1 wherein a polymeric adhesive secures the first chip to said substrate.

8. (original) The semiconductor device of claim 1 wherein bond wires connect more than one chip to said substrate.

9. (original) The semiconductor device of claim 1 wherein said substrate is a BGA package substrate.

10. (original) The device of claim 1 wherein said metal standoffs have a uniform height.

11. (original) The device of claim 1 wherein said supporting chips include copper bond pads having aluminum caps.